# Panasonic

Zener Diode

## DZ2J091×0L Silicon epitaxial planar type

### For constant voltage / For surge absorption circuit

- Features
- · Excellent rising characteristics of zener current Iz
- Low zener operating resistance Rz
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: LJ or LU

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#### Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C					
Parameter	Symbol	Rating			
Repetitive peak forward current	IFRM	200			
Total power dissipation <sup>*1</sup>	PT	200			

Total power dissipation	ΓI	200	11177
Electrostatic discharge *2	ESD	±8	kV
Junction temperature	Tj	150	С°
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tsta	-55 to +150	°C

Note) \*1 Mounted on glass epoxy print board ( 45 mm × 45 mm × 1 mm ) Solder in ( Recommended land pattern )

\*2 Test method : IEC61000\_4\_2

(C = 150 pF, R = 330  $\Omega$ , Contact discharge : 10 times )

#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

$\blacksquare$ Electrical Characteristics Ta = 25 °C	±3°C					
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage <sup>*1, *2</sup>	VZ	IZ = 5 mA	8.65		9.56	V
Zener operating resistance	RZ	IZ = 5 mA			20	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			60	Ω
Reverse current	IR	VR = 6 V			0.1	μA
Temperature coefficient of zener voltage *3	SZ	IZ = 5 mA		5.8		mV/°C

Unit

mA

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. Absolute frequency of input and output is 5 MHz.

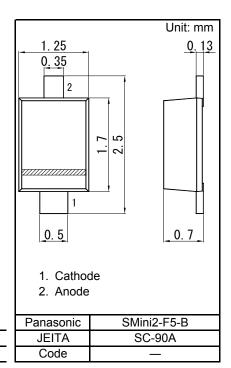
3. \*1 The temperature must be controlled 25 °C for VZ mesurement.

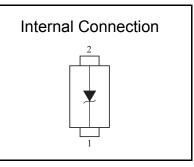
VZ value measured at other temperature must be adjusted to VZ (25 °C).

\*2 VZ guaranted 20 ms after current flow Rank classification

\*3 Tj = 25 °C to 150 °C

k classification				
Code	М	0		
Rank	М	No-rank		
VZ	8.87 to 9.33	8.65 to 9.56		
Marking symbol	LU	LJ		

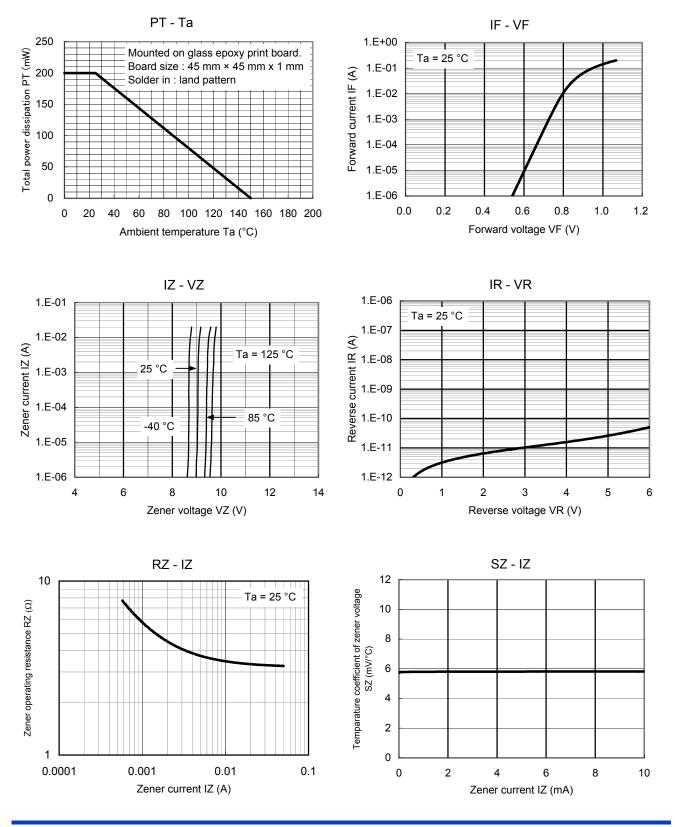






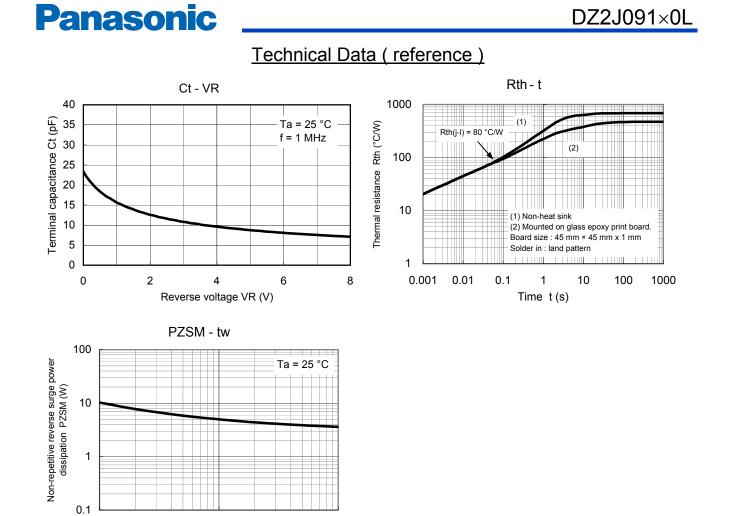
Zener Diode DZ2J091×0L

## Technical Data (reference)



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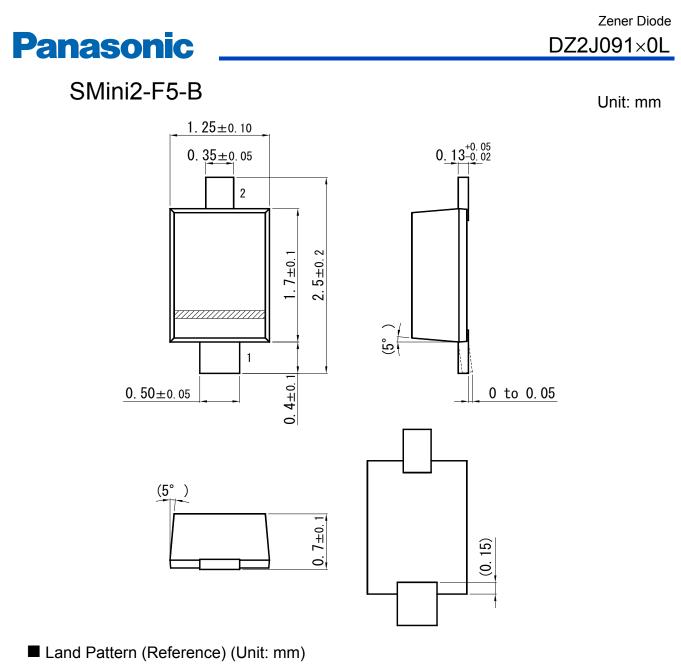
10000

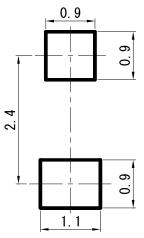
Zener Diode

100

1000

Pulse width tw (µs)





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